HF / VHF power LDMOS transistor

AMPLEON

Rev. 2 — 13 June 2022

Product data sheet

1. Product profile

1.1 General description

A 1200 W LDMOS power transistor for broadcast applications and industrial applications in the HF to 700 MHz band.

Table 1. Application information

Test signal	f	V _{DS}	PL	Gp	ησ
	(MHz)	(V)	(W)	(dB)	(%)
CW pulsed [1]	225	50	1200	25.5	80.0
CW pulsed [2]	352	50	1150	25.0	79.6
CW [2]	352	50	1150	23.6	76.7
CW [3]	500	45	800	22.3	71.6
CW [4]	650	50	1000	20.0	66.2

^[1] On production test circuit t_p = 100 μ s; δ = 10 %.

1.2 Features and benefits

- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (10 MHz to 700 MHz)
- For RoHS compliance see the product details on the Ampleon website

1.3 Applications

- Industrial, scientific and medical applications
- Broadcast transmitter applications

^[2] AR191160.

^[3] AR191195.

^[4] AR201049.

HF / VHF power LDMOS transistor

2. Pinning information

Table 2. Pinning

Description	Simplified outline	Graphic symbol
drain1		
drain2	1 2	1
gate1	5	
gate2	3 4	3 — 5
source	[1]	4 7
		'⊢¬
		2 sym117
	drain1 drain2 gate1 gate2	drain1 drain2 gate1 gate2

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLF978P	-	flanged balanced ceramic package; 2 mounting holes; 4 leads	SOT539A

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	108	٧
V_{GS}	gate-source voltage		-6	+11	٧
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

^[1] Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

5. Thermal characteristics

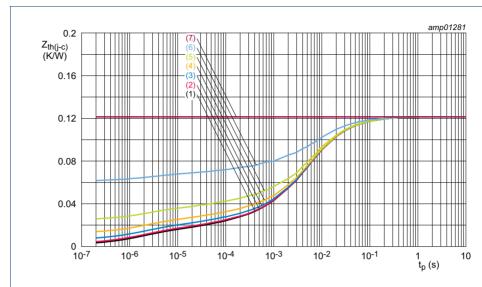
Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	$T_{case} = 90 ^{\circ}C$	0.121	K/W
() -/	transient thermal impedance from junction to case	$T_{case} = 90 ^{\circ}\text{C}; t_p = 100 \mu\text{s}; \ \delta = 10 \%$	0.033	K/W

^[1] $R_{th(j-c)}$ is measured under RF conditions.

[2] See Figure 1.

HF / VHF power LDMOS transistor



- (1) $\delta = 1 \%$
- (2) $\delta = 2 \%$
- (3) $\delta = 5 \%$
- (4) $\delta = 10 \%$
- (5) $\delta = 20 \%$
- (6) $\delta = 50 \%$
- (7) $\delta = 100 \% (DC)$

Fig 1. Transient thermal impedance from junction to case as a function of pulse duration

6. Characteristics

Table 6. DC characteristics

 $T_i = 25$ °C; per section unless otherwise specified.

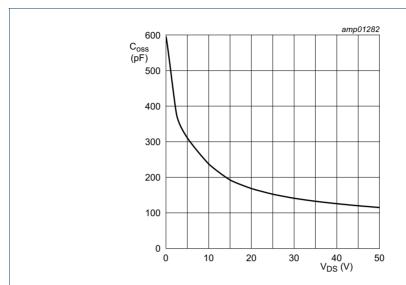
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 3.94 \text{ mA}$	108	-	-	٧
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 394 mA	1.5	2.0	2.5	٧
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 50 V	-	-	2.8	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	54	71.7	-	Α
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	280	nA
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 13.79 \text{ A}$	-	54	-	mΩ

Table 7. AC characteristics

 $T_i = 25$ °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{rs}	feedback capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	1.45	-	pF
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	392	-	pF
C _{oss}	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	115	-	pF

HF / VHF power LDMOS transistor



 $V_{GS} = 0 V$; f = 1 MHz.

Fig 2. Output capacitance as a function of drain-source voltage; typical values per section

Table 8. RF characteristics

Test signal: CW pulsed; t_p = 100 μ s; δ = 10 %; f = 225 MHz; RF performance at V_{DS} = 50 V; I_{Dq} = 50 mA per section; T_{case} = 25 °C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P _L = 1200 W	23	24.5	-	dB
RLin	input return loss	P _L = 1200 W	-	-20	-12	dB
η _D	drain efficiency	P _L = 1200 W	78	80.6	-	%

4 of 15

HF / VHF power LDMOS transistor

7. Application information

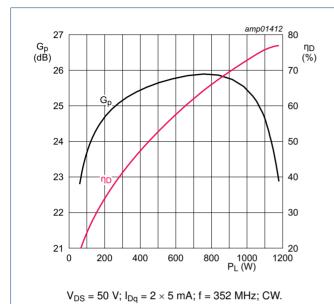
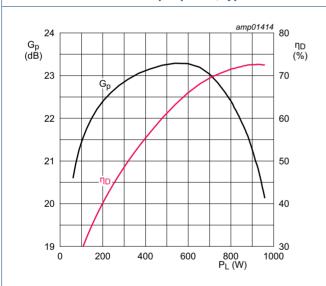
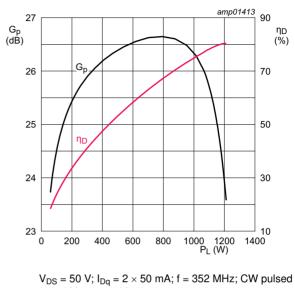


Fig 3. Power gain and drain efficiency on AR191160 as function of output power; typical values

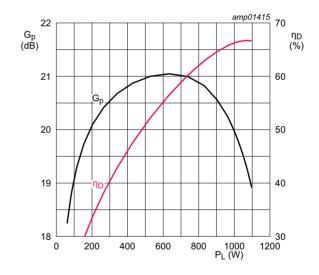


 $V_{DS} = 45 \text{ V; } I_{Dq} = 2 \times 10 \text{ mA; } f = 500 \text{ MHz; CW.}$ Fig 5. Power gain and drain efficiency on AR191195 as function of output power; typical values



 V_{DS} = 50 V; I_{Dq} = 2 × 50 mA; f = 352 MHz; CW pulsed (t_p = 100 μ s; δ = 10 %).

Fig 4. Power gain and drain efficiency on AR191160 as function of output power; typical values



 V_{DS} = 50 V; I_{Dq} = 2 × 10 mA; f = 650 MHz; CW.

Fig 6. Power gain and drain efficiency on AR201049 as function of output power; typical values

HF / VHF power LDMOS transistor

8. Test information

8.1 Ruggedness in class-AB operation

The BLF978P is capable of withstanding a load mismatch corresponding to VSWR = 40 : 1 through all phases under the following conditions: V_{DS} = 50 V; I_{Dq} = 50 mA per section; P_L = 1200 W; f = 225 MHz; CW pulsed (t_p = 100 μ s; δ = 10 %).

8.2 Impedance information

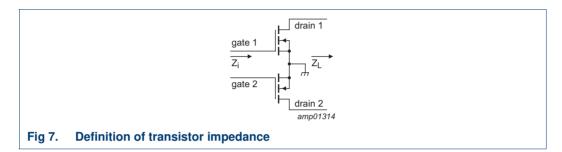


Table 9. Typical push-pull impedance

Simulated Z_i and Z_L device impedance; impedance info at $V_{DS} = 50 \text{ V}$ and $P_L = 1200 \text{ W}$.

f	Z _i	Z_L
(MHz)	(Ω)	(Ω)
225	1.1 – j4.4	3.7 + j1.1

6 of 15

HF / VHF power LDMOS transistor

8.3 Test circuit

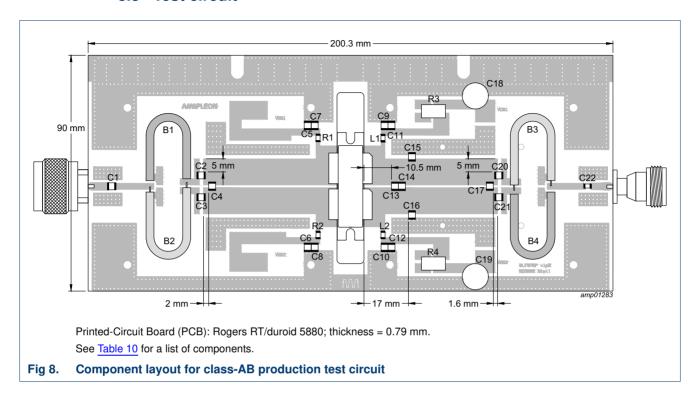


Table 10. List of components

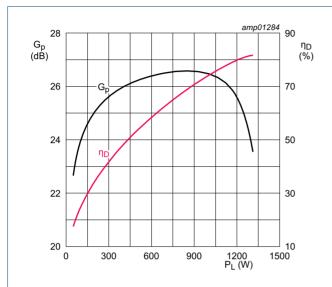
For test circuit see Figure 8.

Component	Description	Value	Remarks
C1, C7, C8, C9, C10, C22	multilayer ceramic chip capacitor	1 nF	ATC 100B
C2, C3	multilayer ceramic chip capacitor	62 pF	ATC 100B
C4	multilayer ceramic chip capacitor	111 pF	ATC 100B
C5, C6, C11, C12	multilayer ceramic chip capacitor	4.7 μF, 100 V	C3225X7S2A475K200AE
C13, C14, C20, C21	multilayer ceramic chip capacitor	47 pF	ATC 100B
C15, C16	multilayer ceramic chip capacitor	43 pF	ATC 100B
C17	multilayer ceramic chip capacitor	51 pF	ATC 100B
C18, C19	electrolytic capacitor	1500 μF, 80 V	
L1, L2	air core inductor	17.5 nH	B06TJLB
R1, R2	SMD resistor	5.1 Ω	SMD 1206
R3, R4	shunt resistor	0.01 Ω	Ohmite: FC4L110R010FER
B1, B2, B3, B4	coaxial line	$50~\Omega,58~\text{mm}$	HUBER+SUHNER: EZ-141-AL-TP-M17

HF / VHF power LDMOS transistor

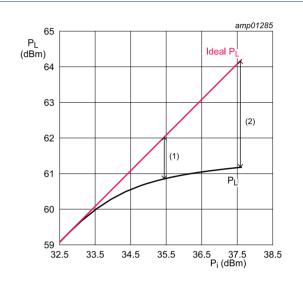
8.4 Graphical data

8.4.1 1-Tone CW pulsed



 V_{DS} = 50 V; I_{Dq} = 2 × 50 mA; f = 225 MHz; t_p = 100 μs ; δ = 10 %.

Fig 9. Power gain and drain efficiency as function of output power; typical values



 $\delta = 10 \%$. (1) $P_{L(1dB)} = 60.79 \text{ dBm } (1200 \text{ W})$

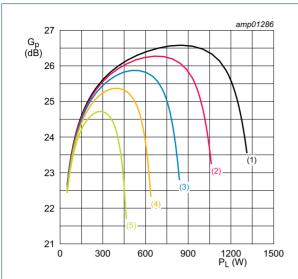
 V_{DS} = 50 V; I_{Dq} = 2 \times 50 mA; f = 225 MHz; t_p = 100 $\mu s;$

(2) $P_{L(3dB)} = 61.17 \text{ dBm } (1310 \text{ W})$

Fig 10. Output power as a function of input power; typical values

8 of 15

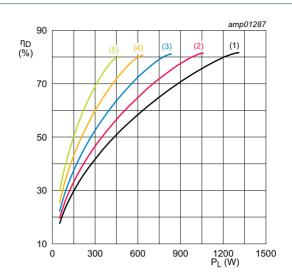
HF / VHF power LDMOS transistor



 I_{Da} = 2 × 50 mA; f = 225 MHz; t_{D} = 100 μ s; δ = 10 %.

- (1) $V_{DS} = 50 \text{ V}$
- (2) $V_{DS} = 45 \text{ V}$
- (3) $V_{DS} = 40 \text{ V}$
- (4) $V_{DS} = 35 \text{ V}$
- (5) $V_{DS} = 30 \text{ V}$

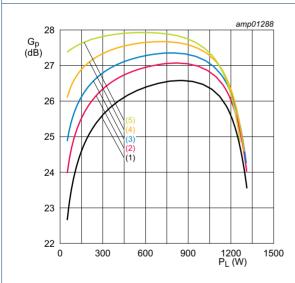
Fig 11. Power gain as a function of output power; typical values



 $I_{Dq} = 2 \times 50$ mA; f = 225 MHz; $t_p = 100$ μ s; $\delta = 10$ %.

- (1) $V_{DS} = 50 \text{ V}$
- (2) $V_{DS} = 45 \text{ V}$
- (3) $V_{DS} = 40 \text{ V}$
- (4) $V_{DS} = 35 \text{ V}$
- (5) $V_{DS} = 30 \text{ V}$

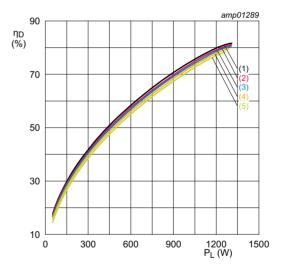
Fig 12. Drain efficiency as a function of output power; typical values



 V_{DS} = 50 V; f = 225 MHz; t_p = 100 μ s; δ = 10 %.

- (1) $I_{Dq} = 2 \times 50 \text{ mA}$
- (2) $I_{Dq} = 2 \times 200 \text{ mA}$
- (3) $I_{Dq} = 2 \times 400 \text{ mA}$
- (4) $I_{Dq} = 2 \times 800 \text{ mA}$
- (5) $I_{Dq} = 2 \times 1400 \text{ mA}$

Fig 13. Power gain as a function of output power; typical values

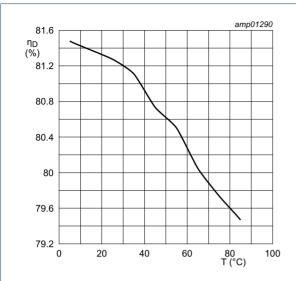


 V_{DS} = 50 V; f = 225 MHz; t_p = 100 μ s; δ = 10 %.

- (1) $I_{Dq} = 2 \times 50 \text{ mA}$
- (2) $I_{Dq} = 2 \times 200 \text{ mA}$
- (3) $I_{Dq} = 2 \times 400 \text{ mA}$
- (4) $I_{Dq} = 2 \times 800 \text{ mA}$
- (5) $I_{Dq} = 2 \times 1400 \text{ mA}$

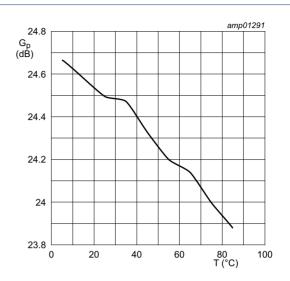
Fig 14. Drain efficiency as a function of output power; typical values

HF / VHF power LDMOS transistor



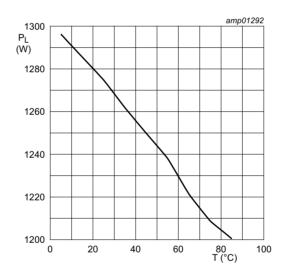
 V_{DS} = 50 V; I_{Dq} = 2 \times 50 mA; f = 225 MHz; at $P_{L(2dB)}.$

Fig 15. Drain efficiency as a function of temperature; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 2 \times 50 \text{ mA}; f = 225 \text{ MHz}; at P_{L(2dB)}.$

Fig 16. Power gain as a function of temperature; typical values



 V_{DS} = 50 V; I_{Dq} = 2 × 50 mA; f = 225 MHz; at $P_{L(2dB)}$.

Fig 17. Output power as a function of temperature; typical values

HF / VHF power LDMOS transistor

9. Package outline

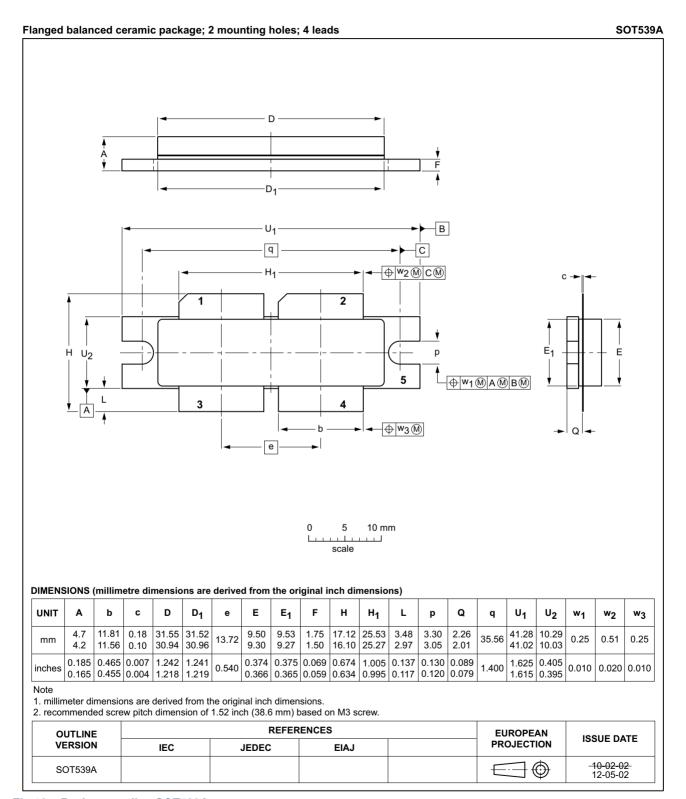


Fig 18. Package outline SOT539A

HF / VHF power LDMOS transistor

10. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 11. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

- [1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V.
- [2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V.

11. Abbreviations

Table 12. Abbreviations

Acronym	Description
CW	Continuous Wave
HF	High Frequency
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MTF	Median Time to Failure
RoHS	Restriction of Hazardous Substances
SMD	Surface Mounted Device
VHF	Very High Frequency
VSWR	Voltage Standing Wave Ratio

12. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF978P v.2	20220613	Product data sheet	-	BLF978P v.1
Modifications:	Section 8.1 on page 6: changed value of VSWR from 13:1 to 40:1			
	 <u>Section 13.2 on page 13</u>: updated section <u>Section 13.3 on page 13</u>: updated section 			
BLF978P v.1	20200403	Product data sheet	-	-

HF / VHF power LDMOS transistor

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition	
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.	
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.	
Product [short] data sheet	Production	This document contains the product specification.	

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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HF / VHF power LDMOS transistor

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HF / VHF power LDMOS transistor

15. Contents

1	Product profile
1.1	General description 1
1.2	Features and benefits
1.3	Applications
2	Pinning information 2
3	Ordering information 2
4	Limiting values 2
5	Thermal characteristics 2
6	Characteristics
7	Application information 5
8	Test information 6
8.1	Ruggedness in class-AB operation 6
8.2	Impedance information 6
8.3	Test circuit
8.4	Graphical data 8
8.4.1	1-Tone CW pulsed 8
9	Package outline
10	Handling information 12
11	Abbreviations12
12	Revision history 12
13	Legal information
13.1	Data sheet status
13.2	Definitions
13.3	Disclaimers
13.4	Trademarks14
14	Contact information 14
15	Contents

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